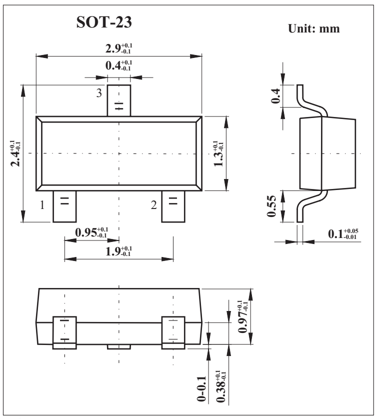
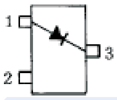
Silicon Epitaxial Planar Type

1SS307

■ Features

- ● Low forward voltage :V_F =1.0 V(Typ)
- ● Low reverse Current :I_R= 0.1 nA (Typ)
- ● Small total capacitance :C_T = 3.0 pF(Typ)





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Average forward current	I_O	100	mA
Maximum (peak) forward current	I_{FM}	300	mA
Surge current (10 ms)	I_{FSM}	2	A
Power dissipation	P	150	mW
Junction Temperature	T_j	125	℃
Storage Temperature	T_{stg}	-55 + 125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 100 mA		1.0	1.3	V
Reverse current	I_R	V_R = 30 V		0.1	10	nA
Total capacitance	C_T	V_R = 0, f = 1.0 MHz		3.0	6.0	pF

■ Marking

Marking	C9